



PTO/SB/08a/b (08-03)
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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/602,716-Conf. #9955
				Filing Date	June 25, 2003
				First Named Inventor	Chandra Mouli
				Art Unit	2811
				Examiner Name	D. Kang
Sheet	1	of	1	Attorney Docket Number	M4065.0904/P904

U.S. PATENT DOCUMENTS					
Examiner Initials [*]	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
AK	AA	2002/0190287	12/19/2002	Mann et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
AK	BA	EP 0 798 785	10/01/1997			
AK	BB	JP 01-232765	09/18/1989			X

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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
dm	CA	Kim, K.T. et al. – "Tungsten Silicide/Titanium Nitride Compound Gate," June 4, 1990, Symposium on VLSI Technology, Honolulu, June 4-7, 1990, New York, IEEE, US, pgs 115-116.			
	CB	Long, Wei et al. – "Dual-Material Gate (DMG) Field Effect Transistor," May 1999, IEEE Transactions on Electron Devices, IEEE Inc. New York, US, pgs. 865-870.			
	CC	Ponomarev, Y.V. et al. – "Gate-Workfunction Engineering Using Poly-(Si,Ge) for High-Performance 0.18 μ m CMOS Technology," International Electron Devices Meeting 1997, IEDM Technical Digest, Washington, DC, Dec. 7-10, 1997, New York, NY, IEEE, US, 12/7/1997, pgs. 829-832.			
	CD	Yagishita, Atsushi et al. – "Dynamic Threshold Voltage Damascene Metal Gate MOSFET (DT-DMG-MOS) Technology for Very Low Voltage Operation of Under 0.7 V," IEEE Transactions on Electron Devices, IEEE Inc. New York, US, vol. 49, no. 3, March 2002, pgs. 422-428.			
	CE	International Search Report dated 11/30/2004.			

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Examiner Signature		Date Considered	02-22-05
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Nm	CA	Nadia Lifshitz - "Dependence of the Work-Function Difference Between the Polysilicon Gate and Silicon Substrate on the Doping Level in Polysilicon," IEEE Transactions on Electron Devices, Vol. Ed-32, No. 3, March 1985.	
	CB	Tsu-Jae King et al. - "Electrical Properties of Heavily Doped Polycrystalline Silicon-Germanium Films," IEEE Transactions on Electron Devices, Vol. 41, No. 2, February 1994.	
	CC	Sunetra Mendis et al. - "CMOS Active Pixel Image Sensor," IEEE Transactions on Electron Devices, Vol. 41, No. 3, March 1994.	
	CD	R. H. Nixon et al. - "256 x 256 CMOS Active Pixel Sensor Camera-on-a-Chip," IEEE Journal of Solid-State Circuits, Vol. 31, No. 12, December 1996.	

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Kangster

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